Diode Semiconductor Device - Page 1 of 1



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Inclosure Mat	erial:
Glass	
Overall Lengt	h:
Between 0.130	0 inches and 0.260 inches
Terminal Leng	gth:
Between 0.900	0 inches and 1.300 inches
Overall Diame	eter:
Between 0.110	0 inches and 0.180 inches
Joint Electror	nic Device Engineering Council/jedec/case Outline Designation:
Do-41	
Mounting Met	thod:
Terminal	
Semiconduct	or Material:
Silicon	
Voltage Ratin	g In Volts Per Characteristic:
600.0 working	peak reverse voltage
Current Ratin	g Per Characteristic:
80.00 amperes	s forward current, average preset
Maximum Op	erating Tempurature Per Measurement Point:
175.0 degrees	celsius junction
Test Data Doo	cument:
81349-mil-s-19	9500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; exclud	les commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental	and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type	e And Quantity:
2 uninsulated v	wire lead
Specification	Data:
81349-mil-s-1§	9500/411 government specification
Shelf Life:	
N/a	
Unit Of Measu	ure:
Demilitarizatio	on:
No	
Fiig:	
A110a0	